

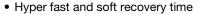
Vishay Semiconductors

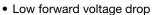
Hyperfast Rectifier, 30 A FRED Pt®



PRIMARY CHARACTERISTICS				
I _{F(AV)}	30 A			
V_{R}	650 V			
V _F at I _F at 125 °C	1.6 V			
t _{rr}	27 ns			
T _J max.	175 °C			
Package	2L TO-220AC			
Circuit configuration	Single			

FEATURES









• True 2 pin package

 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



ROHS COMPLIANT HALOGEN FREE

DESCRIPTION / APPLICATIONS

Ultra low V_F , soft-switching hyper fast rectifiers optimized for discontinuous (critical) mode (DCM) power factor correction (PFC).

The minimized conduction loss, optimized stored charge and low recovery current minimized the switching losses and reduce over dissipation in the switching element and snubbers.

The device is also intended for use as a freewheeling diode in power supplies and other power switching applications.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Repetitive peak reverse voltage	V_{RRM}		650	V	
Average rectified forward current	I _{F(AV)}	T _C = 120 °C	30	۸	
Non-repetitive peak surge current	I _{FSM}	T _C = 25 °C	210	A	
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 250 μA	650	-	-	
Forward voltage V _F	V	I _F = 30 A	-	2.1	2.5	V
	VF	I _F = 30 A, T _J = 125 °C	-	1.6	1.7	
Doverse leekage current	1	$V_R = V_R$ rated	-	0.02	30	μA
Reverse leakage current I _R		$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	50	300	μΑ
Junction capacitance	C _T	V _R = 200 V	-	22	-	pF
Series inductance	L _S	L _S Measured lead to lead 5 mm from package body - 8.0 - n		nH		



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t _{rr}	T _J = 25 °C	I _F = 1 A dI _F /dt = 100 A/μs V _R = 30 V	-	35	-	- ns
		T _J = 25 °C		-	27	-	
		T _J = 125 °C		-	88	-	
Peak recovery current I _{RRM}		T _J = 25 °C	$I_F = 30 \text{ A}$ $dI_F/dt = 1000 \text{ A/µs}$ $V_R = 400 \text{ V}$	-	15	-	Α
	IRRM	T _J = 125 °C		-	24	-	^
Deverse vecesses shows	Reverse recovery charge Q _{rr}	T _J = 25 °C		-	330	-	nC
neverse recovery charge		T _J = 125 °C		ı	1350	ı	iiC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction to case	R_{thJC}		-	1.0	1.3	
Thermal resistance, junction to ambient	R_{thJA}	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heat sink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	-	0.5	
Weight			-	0.2	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0		12	kgf · cm
wounting torque			(5.0)	_	(10)	(lbf · in)
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C
Marking device		Case style: 2L TO-220AC	ETX3007			

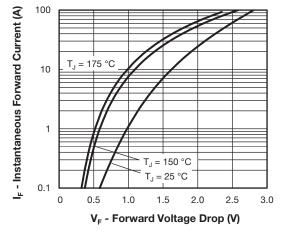


Fig. 1 - Typical Forward Voltage Drop Characteristics

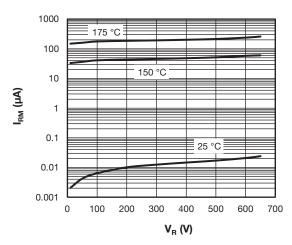


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



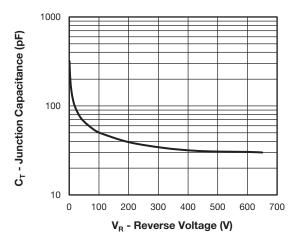


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

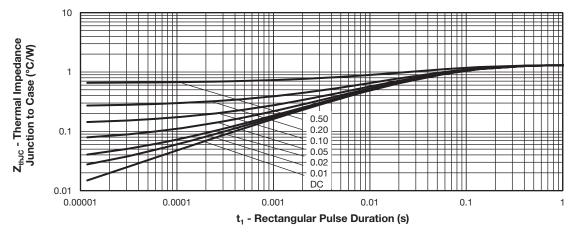


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

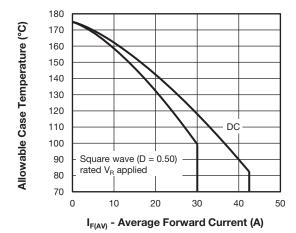


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

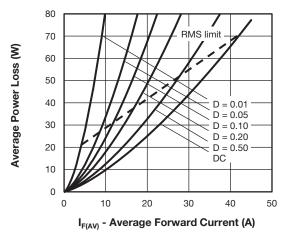
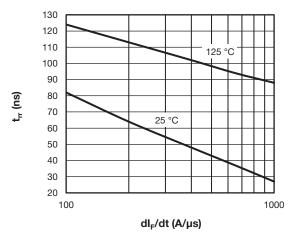


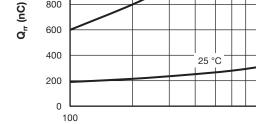
Fig. 6 - Forward Power Loss Characteristics

1000

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125 °C

1400

1200

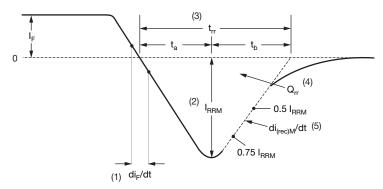
1000

800

Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

Fig. 8 - Typical Reverse Recovery Time vs. dl_F/dt

dI_F/dt (A/μs)



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $t_{\rm rr}$ reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

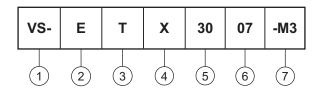
Fig. 9 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - E = single diode

3 - Package:

T = TO-220AC

4 - X = hyper fast recovery

5 - Current rating (30 = 30 A)

6 - Voltage rating (07 = 650 V)

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-ETX3007-M3	50	1000	Antistatic plastic tube			

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?96156</u>				
Part marking information	www.vishay.com/doc?95391			
SPICE model	www.vishay.com/doc?96532			



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